

What is claimed is:

1. A method of fabricating a semiconductor wafer, comprising:
- (a) polishing a semiconductor wafer with a polishing pad; and
 - (b) disposing a volume of a nonaqueous solvent onto said semiconductor
- 5 wafer.

2. The method of claim 1, wherein:
- (a) includes disposing a volume of an aqueous slurry containing an
- 10 abrasive material onto said semiconductor wafer.

3. The method of claim 1, wherein:
- 15 said polishing pad is in contact with said semiconductor wafer when said nonaqueous solvent is disposed onto said semiconductor wafer.

4. The method of claim 2, further comprising:
- (c) mixing said aqueous slurry and said nonaqueous solvent in a mixing
- 20 unit so as to create an aqueous slurry/nonaqueous solvent mixture prior to being disposed onto said semiconductor wafer.

5. The method of claim 4, wherein:
- (c) includes increasing the weight % of said nonaqueous solvent in said
- aqueous slurry/nonaqueous solvent mixture during said polishing of said semiconductor wafer.

6. The method of claim 5, wherein:
said weight % of said nonaqueous solvent in said aqueous
slurry/nonaqueous solvent mixture is increased until said aqueous
slurry/nonaqueous solvent mixture is substantially free of said aqueous slurry.

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7. The method of claim 1, wherein:
said nonaqueous solvent includes an ammine.

8. The method of clam 1, wherein:
said nonaqueous solvent includes dimethylsulfoxide.

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SpA2 9. The method of claim 1, wherein:
said nonaqueous solvent includes Nnpropanalamide.

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10. The method of claim 1, wherein:
said nonaqueous solvent includes analine.

11. The method of claim 1, wherein:
said nonaqueous solvent includes N,N-dimethlyanaline.

12. A method of fabricating a semiconductor wafer, comprising:
(a) subjecting a front side of said semiconductor wafer to chemical
mechanical polishing; and
(b) disposing a volume of a nonaqueous solvent onto said front side of
5 said semiconductor wafer.

13. The method of claim 12, wherein:
said nonaqueous solvent includes an ammine.

10 14. The method of claim 12, wherein:
said nonaqueous solvent includes dimethylsulfoxide.

15 ~~15. The method of claim 12, wherein:
said nonaqueous solvent includes Npropanalamide.~~

16. The method of claim 12, wherein:
said nonaqueous solvent includes analine.

20 17. The method of claim 12, wherein:
said nonaqueous solvent includes N,N-dimethlyanaline.

18. An arrangement for fabricating a semiconductor wafer, comprising:
a polishing pad positioned in contact with a side of said semiconductor wafer;

a chemical slurry system for storing an aqueous slurry, said chemical
5 slurry system being operatively coupled to said semiconductor wafer so that said
chemical slurry system can dispose a volume of said aqueous slurry onto said
side of said semiconductor wafer; and

a nonaqueous solvent storage system for storing a nonaqueous solvent,
said nonaqueous solvent storage system being operatively coupled to said
10 semiconductor wafer so that said nonaqueous solvent storage system can
dispose a volume of said nonaqueous solvent onto said side of said
semiconductor wafer.

19. The arrangement of claim 18, further comprising:

15 a mixing unit in fluid communication with said chemical slurry system and
said nonaqueous solvent storage system such that said aqueous slurry and said
nonaqueous solvent are mixed in said mixing unit so as to create an aqueous
slurry/nonaqueous solvent mixture prior to being disposed on said side of said
semiconductor wafer.

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20. The arrangement of claim 18, wherein:

said nonaqueous solvent includes a substance selected from the group consisting of dimethylsulfoxide, Nnpropanalamide, analine, N,N-dimethlyanaline, and ammines.

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